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View Online at https://aerobasegroup.com/nsn/5961-01-012-8190
Inclosure Material:
Metal
Overall Length:
1.252 inches
Overall Height:
0.340 inches
Overall Width:
0.700 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-66
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakdown voltage, collector-to-base, emitter open and 100.0 breakdown voltage, collector-to-emitter, base open and 100.0
breakdown voltage, collector-to-emitter, base open and 6.0 breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
7.00 amperes source cutoff current
Power Rating Per Characteristic:
40.0 watts small-signal input power, common-collector absolute
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
82577-928846 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing) and 82577-928418 drawing
(this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any
specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 uninsulated wire lead and 1 case
Shelf Life:
N/a
Unit Of Measure:

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